

0.4A, 400V, 3.600 Ohm, N-Channel Power MOSFET

These are N-Channel enhancement mode silicon gate power field effect transistors. They are advanced power MOSFETs designed, tested, and guaranteed to withstand a specified level of energy in the breakdown avalanche mode of operation. All of these power MOSFETs are designed for applications such as switching regulators, switching convertors, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. These types can be operated directly from integrated circuits.

Formerly developmental type TA17444.

Ordering Information

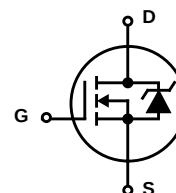
PART NUMBER	PACKAGE	BRAND
IRFD310	HEXDIP	IRFD310

NOTE: When ordering, use the entire part number.

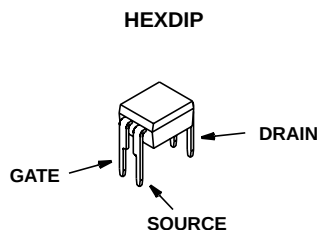
Features

- 0.4A, 400V
- $r_{DS(ON)} = 3.600\Omega$
- Single Pulse Avalanche Energy Rated
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol



Packaging



Absolute Maximum Ratings $T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

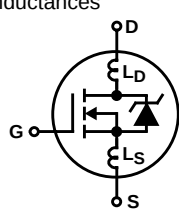
	IRFD310	UNITS
Drain to Source Voltage (Note 1)	V_{DS} 400	V
Drain to Gate Voltage ($R_{GS} = 20\text{k}\Omega$) (Note 1)	V_{DGR} 400	V
Continuous Drain Current	I_D 0.4	A
Pulsed Drain Current (Note 3)	I_{DM} 1.6	A
Gate to Source Voltage	V_{GS} ± 20	V
Maximum Power Dissipation	P_D 1.0	W
Linear Derating Factor	0.008	$\text{W}/^{\circ}\text{C}$
Single Pulse Avalanche Energy Rating (Note 4)	E_{AS} 45	mJ
Operating and Storage Temperature	T_J, T_{STG} -55 to 150	$^{\circ}\text{C}$
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s	T_L 300	$^{\circ}\text{C}$
Package Body for 10s, See Techbrief 334	T_{pkg} 260	$^{\circ}\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. $T_J = 25^{\circ}\text{C}$ to 125°C .

Electrical Specifications $T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V (Figure 9)		400	-	-	V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250μA		2.0	-	4.0	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = Rated BV _{DSS} , V _{GS} = 0V		-	-	25	μA
		V _{DS} = 0.8 x Rated BV _{DSS} , V _{GS} = 0V, T _C = 125°C		-	-	250	μA
On-State Drain Current (Note 2)	I _{D(ON)}	V _{DS} > I _{D(ON)} x r _{DS(ON)MAX} , V _{GS} = 10V		0.4	-	-	A
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20V		-	-	±100	nA
Drain to Source On Resistance (Note 2)	r _{DS(ON)}	I _D = 0.2A, V _{GS} = 10V (Figures 7, 8)		-	3.3	3.6	Ω
Forward Transconductance (Note 2)	g _{fs}	V _{DS} ≥ 10V, I _D = 1.2A (Figure 11)		1.0	1.2	-	S
Turn-On Delay Time	t _{d(ON)}	V _{DD} = 0.5 x Rated BV _{DSS} , I _D ≈ 0.4A, R _G = 9.1Ω, V _{GS} = 10V, R _L = 495Ω for V _{DSS} = 200V MOSFET Switching Times are Essentially Independent of Operating Temperature		-	3.0	10	ns
Rise Time	t _r			-	10	20	ns
Turn-Off Delay Time	t _{d(OFF)}			-	5.0	10	ns
Fall Time	t _f			-	8.0	15	ns
Total Gate Charge (Gate to Source + Gate to Drain)	Q _{g(TOT)}	V _{GS} = 10V, I _D = 0.4A, V _{DS} = 0.8 x Rated BV _{DSS} I _{g(REF)} = 1.5mA (Figure 13) Gate Charge is Essentially Independent of Operating Temperature		-	6.0	7.5	nC
Gate to Source Charge	Q _{gs}			-	3.0	-	nC
Gate to Drain “Miller” Charge	Q _{gd}			-	3.0	-	nC
Input Capacitance	C _{ISS}	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz (Figure 10)		-	135	-	pF
Output Capacitance	C _{OSS}			-	35	-	pF
Reverse Transfer Capacitance	C _{RSS}			-	8.0	-	pF
Internal Drain Inductance	L _D	Measured From Drain Lead, 2.0mm (0.08in) From Package to Center of Die	Modified MOSFET Symbol Showing the Internal Device Inductances 	-	4.0	-	nH
Internal Source Inductance	L _S	Measured From the Source Lead, 2.0mm (0.08in) from Package to Source Bonding Pad		-	6.0	-	nH
Thermal Resistance, Junction to Ambient	R _{θJA}	Free Air Operation		-	-	120	°C/W

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Continuous Source to Drain Current	I_{SD}	Modified MOSFET Symbol Showing the Integral Reverse P-N Junction Rectifier	-	-	0.4	A
Pulse Source to Drain Current (Note 3)	I_{SDM}		-	-	1.6	A
Source to Drain Diode Voltage (Note 2)	V_{SD}	$T_J = 25^{\circ}\text{C}$, $I_{SD} = 1.6\text{A}$, $V_{GS} = 0\text{V}$ (Figure 12)	-	-	1.6	V
Reverse Recovery Time	t_{rr}	$T_J = 150^{\circ}\text{C}$, $I_{SD} = 1.6\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	380	-	ns
Reverse Recovery Charge	Q_{RR}	$T_J = 150^{\circ}\text{C}$, $I_{SD} = 1.6\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	2.7	-	μC

NOTES:

- Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
- Repetitive rating: pulse width limited by Max junction temperature.
- $V_{DD} = 40\text{V}$, starting $T_J = 25^{\circ}\text{C}$, $L = 44.89\text{mH}$, $R_G = 50\Omega$, peak $I_{AS} = 1.4\text{A}$.

Typical Performance Curves Unless Otherwise Specified

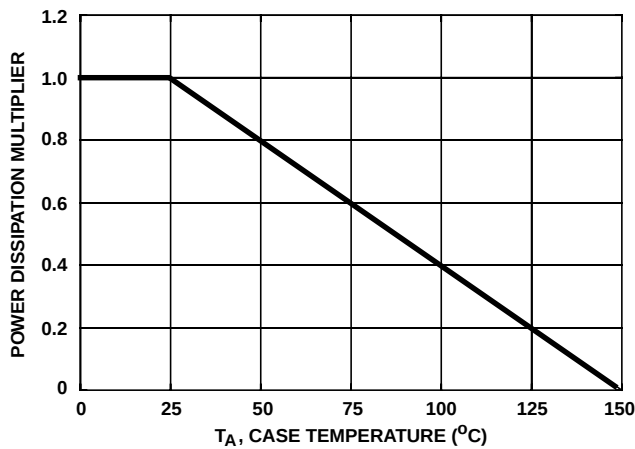


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

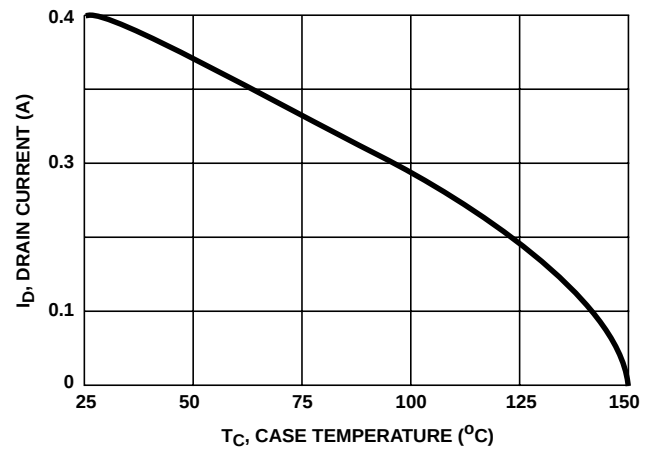


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

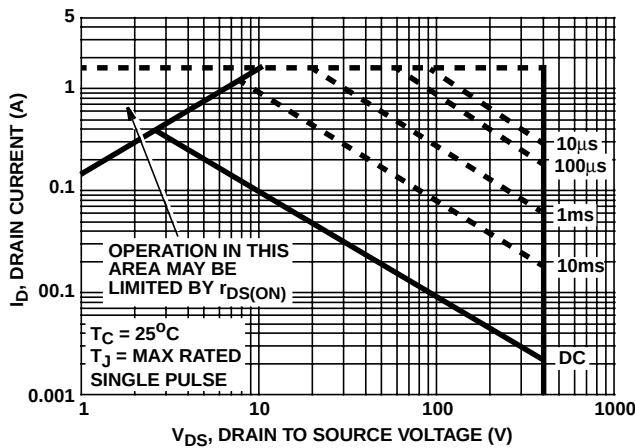


FIGURE 3. FORWARD BIAS SAFE OPERATING AREA

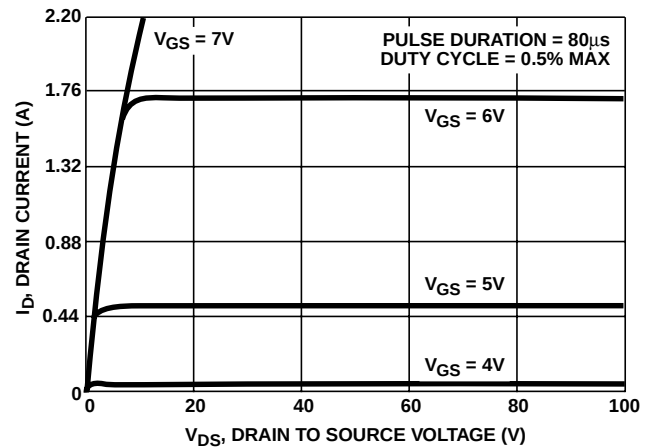


FIGURE 4. OUTPUT CHARACTERISTICS

Typical Performance Curves

Unless Otherwise Specified (Continued)

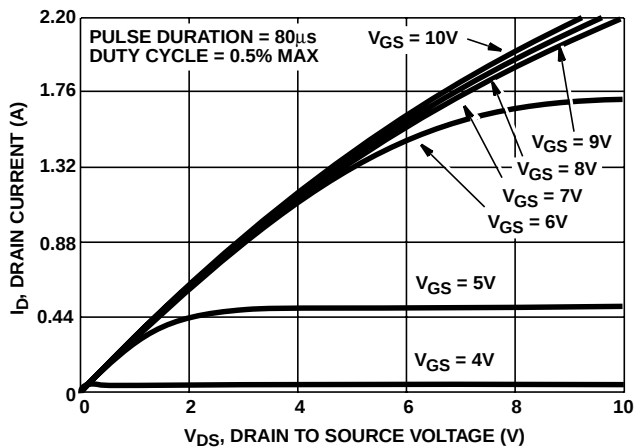


FIGURE 5. SATURATION CHARACTERISTICS

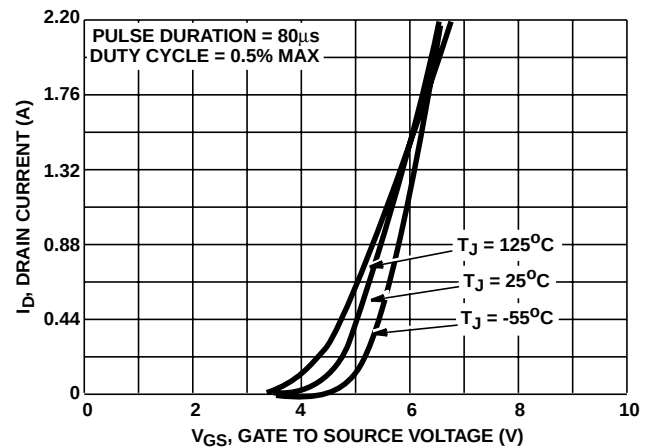


FIGURE 6. TRANSFER CHARACTERISTICS

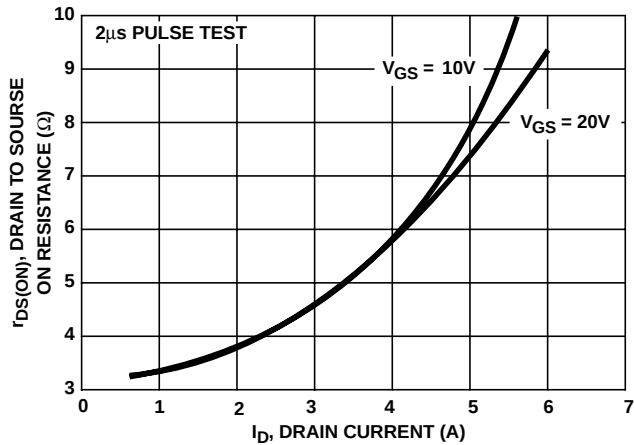


FIGURE 7. DRAIN TO SOURCE ON RESISTANCE vs GATE VOLTAGE AND DRAIN CURRENT

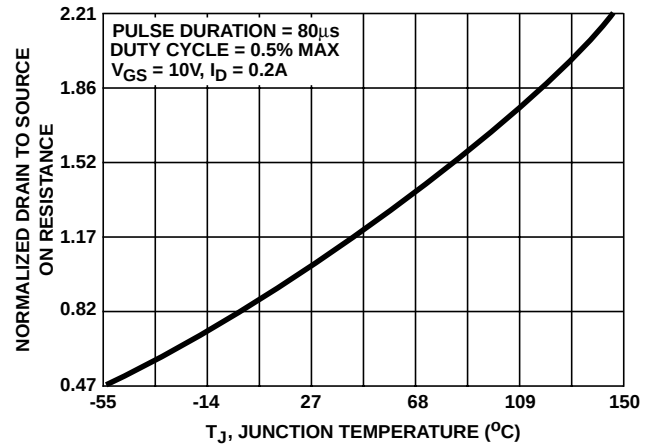


FIGURE 8. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

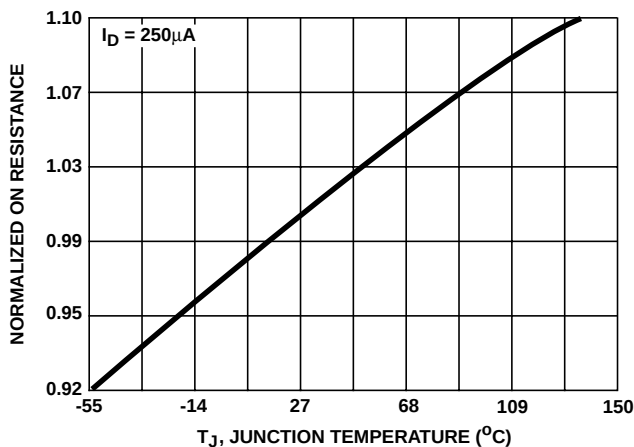


FIGURE 9. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

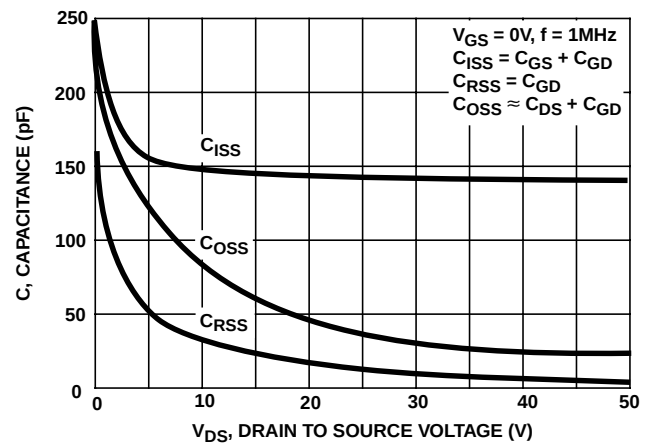


FIGURE 10. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE

Typical Performance Curves Unless Otherwise Specified (Continued)

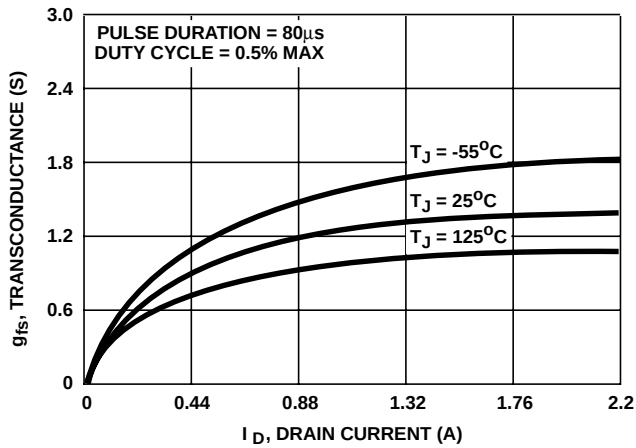


FIGURE 11. TRANSCONDUCTANCE vs DRAIN CURRENT

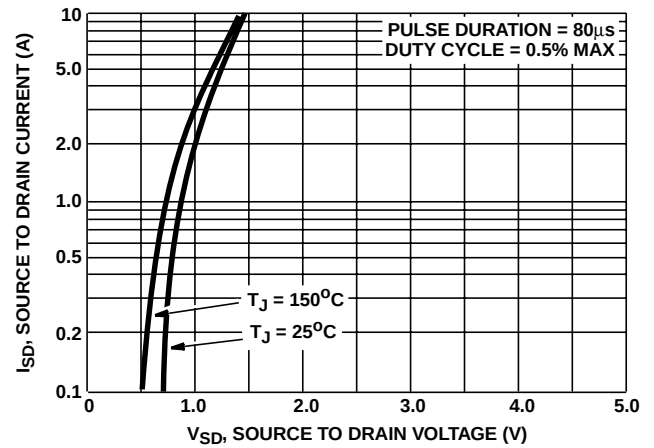


FIGURE 12. SOURCE TO DRAIN DIODE VOLTAGE

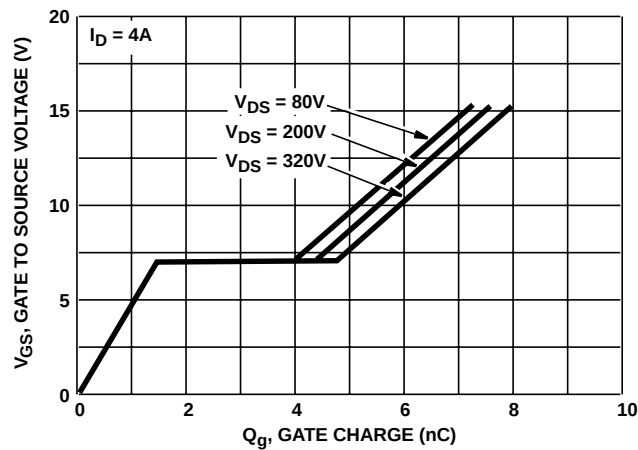


FIGURE 13. GATE TO SOURCE VOLTAGE vs GATE CHARGE

Test Circuits and Waveforms

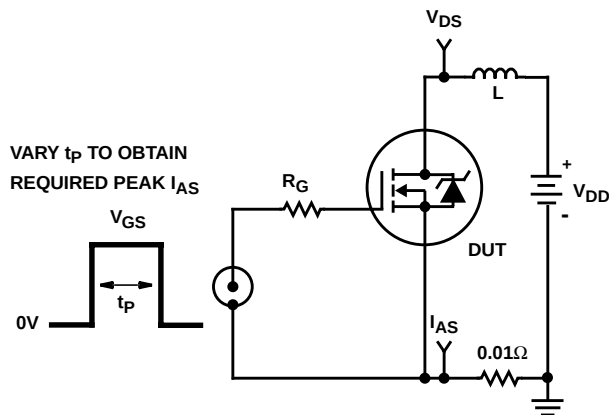


FIGURE 14. UNCLAMPED ENERGY TEST CIRCUIT

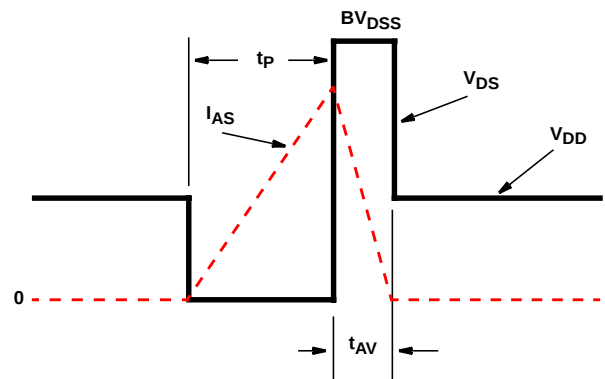


FIGURE 15. UNCLAMPED ENERGY WAVEFORM

Test Circuits and Waveforms (Continued)

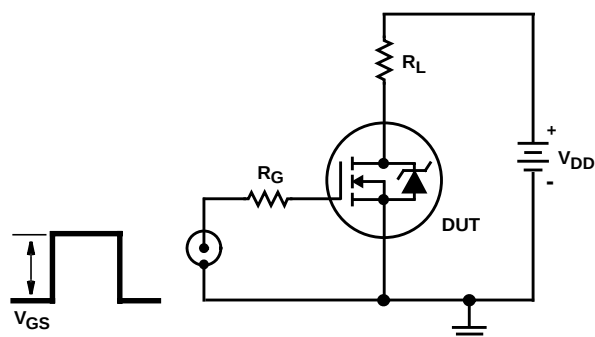


FIGURE 16. SWITCHING TIME TEST CIRCUIT

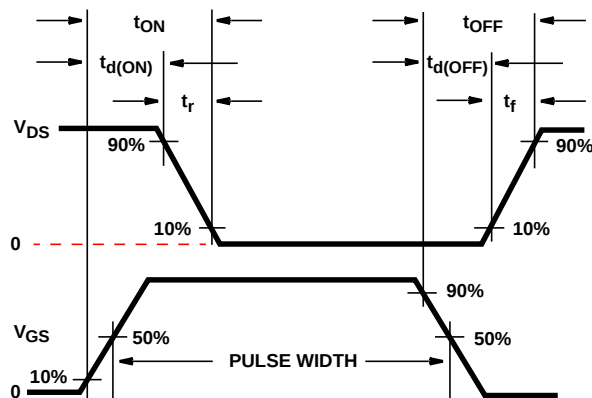


FIGURE 17. GATE CHARGE TEST CIRCUIT

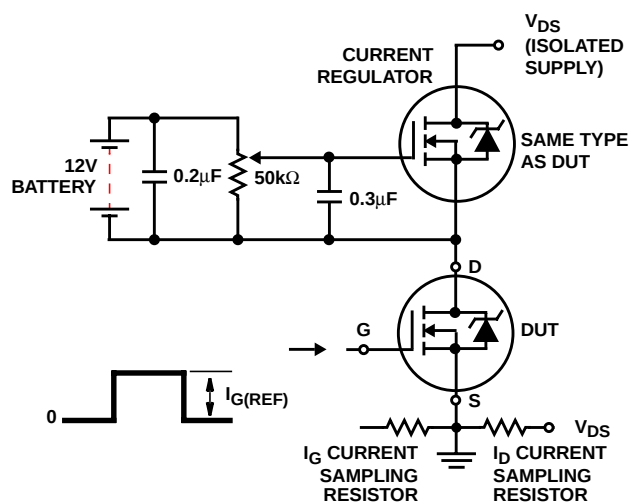


FIGURE 18. GATE CHARGE TEST CIRCUIT

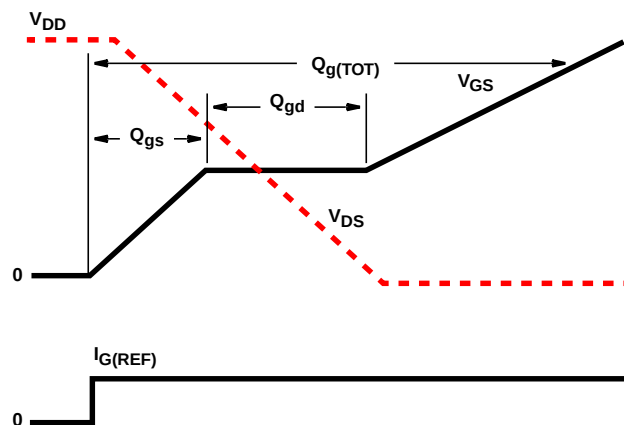


FIGURE 19. GATE CHARGE WAVEFORMS

All Intersil semiconductor products are manufactured, assembled and tested under **ISO9000** quality systems certification.

Intersil semiconductor products are sold by description only. Intersil Corporation reserves the right to make changes in circuit design and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that data sheets are current before placing orders. Information furnished by Intersil is believed to be accurate and reliable. However, no responsibility is assumed by Intersil or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Intersil or its subsidiaries.

For information regarding Intersil Corporation and its products, see web site <http://www.intersil.com>

Sales Office Headquarters

NORTH AMERICA

Intersil Corporation
P. O. Box 883, Mail Stop 53-204
Melbourne, FL 32902
TEL: (407) 724-7000
FAX: (407) 724-7240

EUROPE

Intersil SA
Mercure Center
100, Rue de la Fusée
1130 Brussels, Belgium
TEL: (32) 2.724.2111
FAX: (32) 2.724.22.05

ASIA

Intersil (Taiwan) Ltd.
7F-6, No. 101 Fu Hsing North Road
Taipei, Taiwan
Republic of China
TEL: (886) 2 2716 9310
FAX: (886) 2 2715 3029